

RJL5020DPK

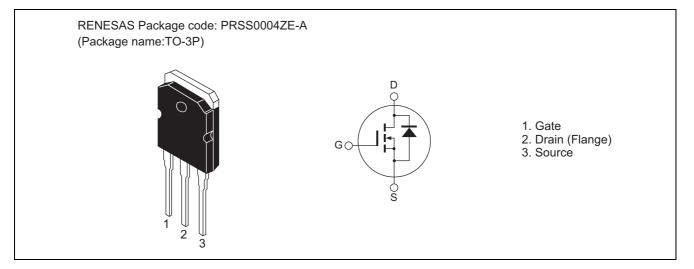
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1733-0400 Rev.4.00 Aug 29, 2008

Features

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	Ι _D	38	А
Drain peak current	Note1 D (pulse)	114	А
Body-drain diode reverse drain current	I _{DR}	38	А
Body-drain diode reverse drain peak current	Note1 DR (pulse)	114	А
Avalanche current	I _{AP} ^{Note3}	12.5	А
Avalanche energy	E _{AR} ^{Note3}	8.6	mJ
Channel dissipation	Pch Note2	200	W
Channel to case thermal impedance	θch-c	0.625	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 $\mu s,$ duty cycle \leq 1%

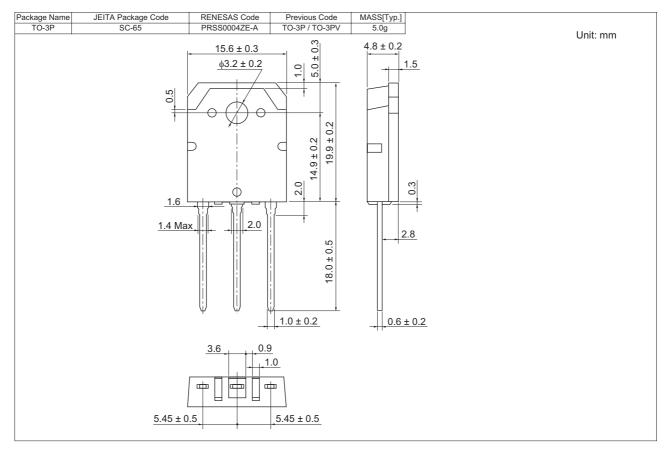
- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

Electrical Characteristics

						(Ta = 25°C)
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	500	—	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	10	μΑ	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}		—	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V _{GS(off)}	1.5	—	4.0	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{\text{DS(on)}}$		0.105	0.135	Ω	$I_D = 19 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	4750	_	pF	V _{DS} = 25 V V _{GS} = 0 f = 1 MHz
Output capacitance	Coss	_	520	_	pF	
Reverse transfer capacitance	Crss	_	61		pF	
Turn-on delay time	t _{d(on)}	_	45	-	ns	$ I_D = 19 \ A \\ V_{GS} = 10 \ V \\ R_L = 13.2 \ \Omega \\ Rg = 10 \ \Omega $
Rise time	tr		90		ns	
Turn-off delay time	t _{d(off)}		215		ns	
Fall time	t _f		154		ns	
Total gate charge	Qg	_	140	_	nC	V _{DD} = 400 V V _{GS} = 10 V I _D = 38 A
Gate to source charge	Qgs		19		nC	
Gate to drain charge	Qgd	_	57		nC	
Body-drain diode forward voltage	V _{DF}	_	0.94	1.60	V	$I_F = 38 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}		170		ns	$I_F = 38 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJL5020DPK-00-T0	360 pcs	Box (Tube)

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